

#### Maximum Ratings and Thermal Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

PARAME	SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V <sub>DS</sub>	20	V
Gate-Source Voltage	V <sub>GS</sub>	+12	V	
Continuous Drain Current	ID	6.0	А	
Pulsed Drain Current (Note 4)		I <sub>DM</sub>	32	А
Power Dissipation	T <sub>a</sub> =25°C		1.25	W
	Derate above 25°C		10	mW/ °C
Operating Junction and Storage	T <sub>J</sub> ,T <sub>STG</sub>	-55~150	°C	
Typical Thermal resistance Junction to Ambient <sup>(Note 3)</sup>		R <sub>θJA</sub>	100	°C/W



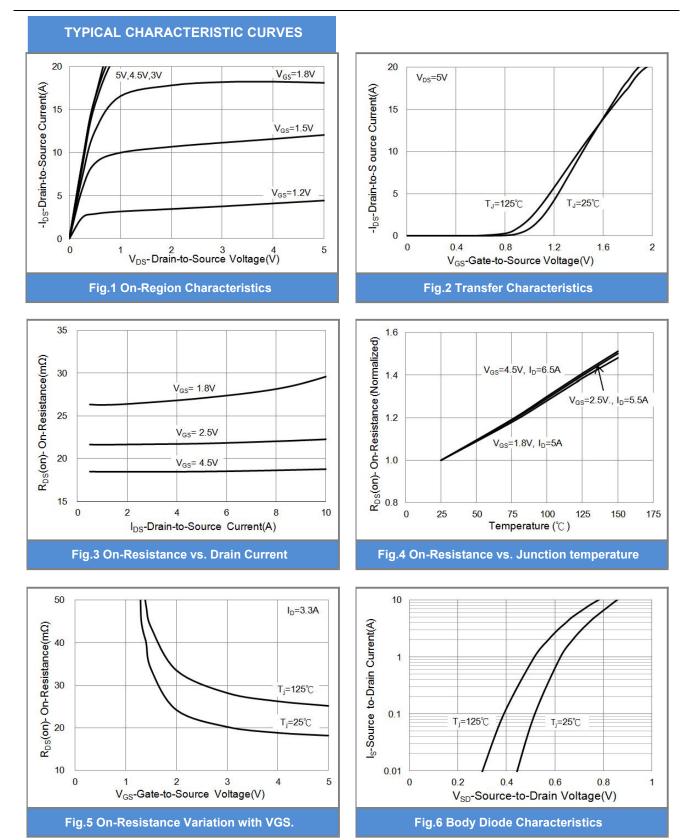
### Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static			·			
Drain-Source Breakdown Voltage	$BV_{DSS}$	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	20	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA	0.4	0.58	1.0	V
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	$V_{GS}$ =4.5V, I <sub>D</sub> =6.0A	-	18.4	25	mΩ
		V <sub>GS</sub> =2.5V, I <sub>D</sub> =5.2A	-	21.5	28	
		V <sub>GS</sub> =1.8V, I <sub>D</sub> =4.5A	-	26.4	34	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =20V, V <sub>GS</sub> =0V	-	-	1	uA
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = <u>+</u> 8V, V <sub>DS</sub> =0V	-	-	<u>+</u> 10	uA
Dynamic						
Total Gate Charge	$Q_{g}$	V <sub>DS</sub> =10V, I <sub>D</sub> =6.0A, V <sub>GS</sub> =4.5V <sup>(Note 1,2)</sup>	-	8.6	-	nC
Gate-Source Charge	$Q_gs$		-	1.06	-	
Gate-Drain Charge	$Q_gd$		-	1.04	-	
Input Capacitance	Ciss	V <sub>DS</sub> =10V, V <sub>GS</sub> =0V, f=1.0MHZ	-	836	-	pF
Output Capacitance	Coss		-	96	-	
Reverse Transfer Capacitance	Crss	I=1.0MHZ	-	80	-	
Switching						
Turn-On Delay Time	td <sub>(on)</sub>		-	24	-	
Turn-On Rise Time	tr	$V_{DD}=10V, I_{D}=1A,$ $V_{GS}=4.5V,$ $R_{G}=3\Omega$ <sup>(Note 1,2)</sup>	-	46	-	ns
Turn-Off Delay Time	td <sub>(off)</sub>		-	0.22	-	us
Turn-Off Fall Time	tf	R <sub>G</sub> -312	-	0.30	-	
Drain-Source Diode						
Maximum Continuous Drain-Source Diode Forward Current	ls		-	-	1.5	A
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =1.0A, V <sub>GS</sub> =0V	-	0.74	1.0	V

NOTES :

- 1. Pulse width <300us, Duty cycle <2%
- 2. Essentially independent of operating temperature typical characteristics.
- 4. The maximum current rating is package limited.







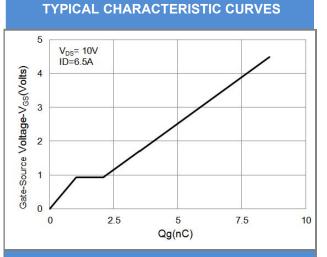
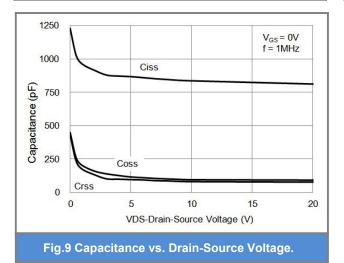
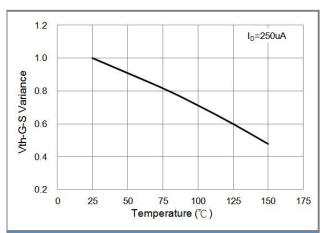


Fig.7 Gate-Charge Characteristics





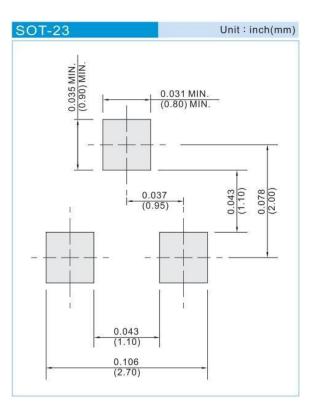




#### PART NO PACKING CODE VERSION

PART NO PACKING CODE	Package Type	Packing type
CSM3416S23	SOT-23	3K pcs / 7" reel

#### MOUNTING PAD LAYOUT





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